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Raman scattering study of Zn/⁺//P/⁺ +/ co-implanted GaAs single crystals

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Abstract

The activation efficiency of zinc impurity co-implanted with P/⁺ +/
ions in GaAs single crystals was studied by Raman scattering (RS) at phonon-
plasmon coupled modes. P/⁺ +/
co-implantation has been found to result
in impurity activation improvement, the optimum electrical parameters of
implanted layers being achieved after sample annealing at 700/spl deg/C.

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